Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
-16V	39mΩ @ V_{GS} = -4.5V	-2.5A
	52mΩ @ V_{GS} = -2.5V	-2.1A
	65mΩ @ V_{GS} = -1.8V	-1.8A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

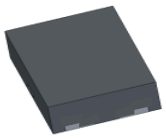
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

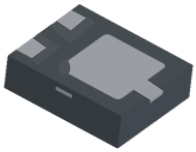
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

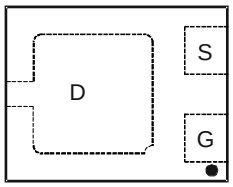
- Case: X2-DFN2015-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



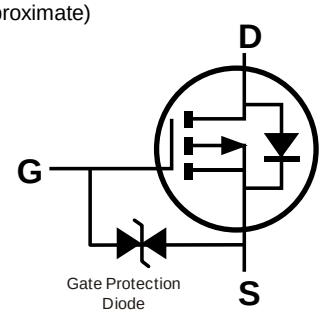
Top View



Bottom View



Internal Schematic
(Top View)



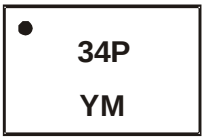
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMG3415UFY4Q-7	X2-DFN2015-3	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



34P = Marking Code
YM = Date Code Marking
Y = Year (ex: C = 2015)
M = Month (ex: 9 = September)

Date Code Key

Year	2009	~	2015	2016	2017	2018	2019	2020	2021
Code	W	~	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-16	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 7) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-2.5 -2.2	A
Pulsed Drain Current (Note 7)			I_{DM}	-12	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P_D	0.65	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	197	°C/W
Total Power Dissipation (Note 7)		P_D	1.35	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	95	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	22	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-16	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -16V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10 ±500	µA nA	V_{GS} = ±8V, V_{DS} = 0V V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	-0.55	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	31	39	mΩ	V_{GS} = -4.5V, I_D = -4.0A
			40	52		V_{GS} = -2.5V, I_D = -3.5A
			51	65		V_{GS} = -1.8V, I_D = -2.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	7.9	—	S	V_{DS} = -5V, I_D = -2.5A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	282	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	152	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	38	—	pF	
Gate Resistance	R_g	—	250	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	10	—	nC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -4A
Gate-Source Charge	Q_{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.4	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	79	—	ns	V_{DS} = -10V, V_{GS} = -4.5V, R_D = 2.5Ω, R_G = 3.0Ω
Turn-On Rise Time	t_R	—	175	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	885	—	ns	
Turn-Off Fall Time	t_F	—	568	—	ns	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

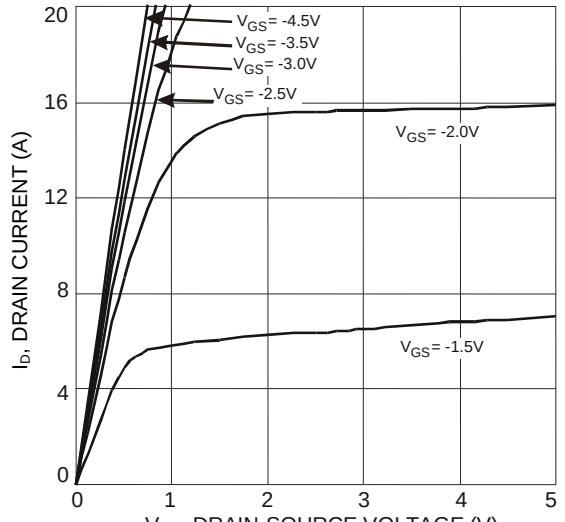


Fig. 1 Typical Output Characteristic

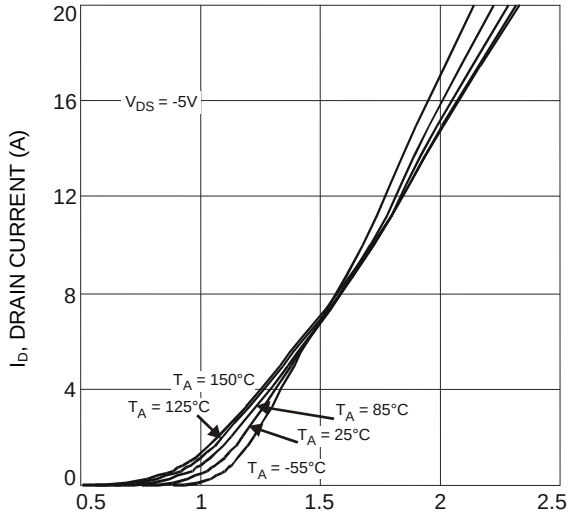


Fig. 2 Typical Transfer Characteristic

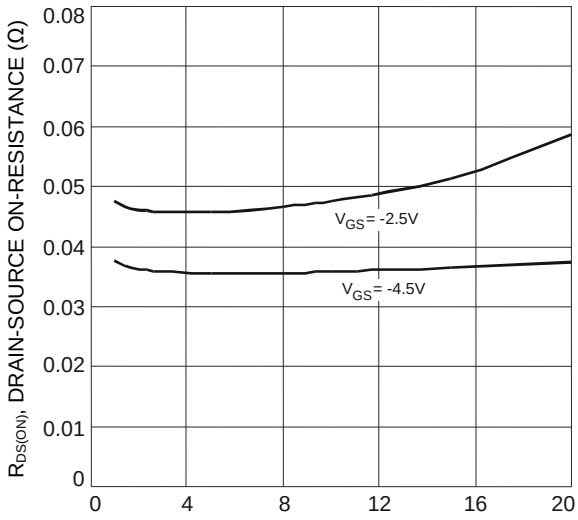


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

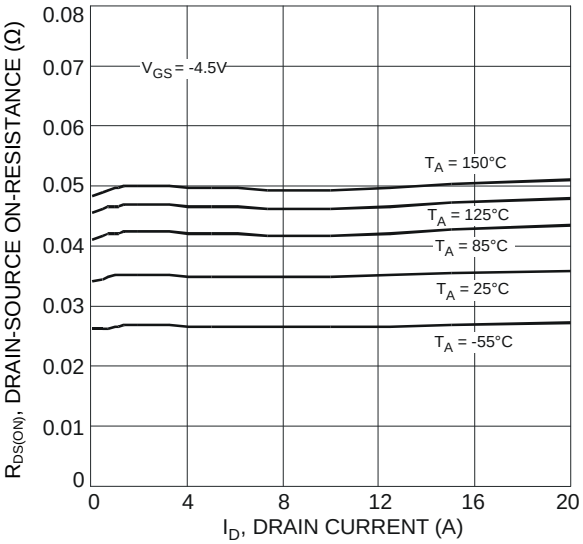


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

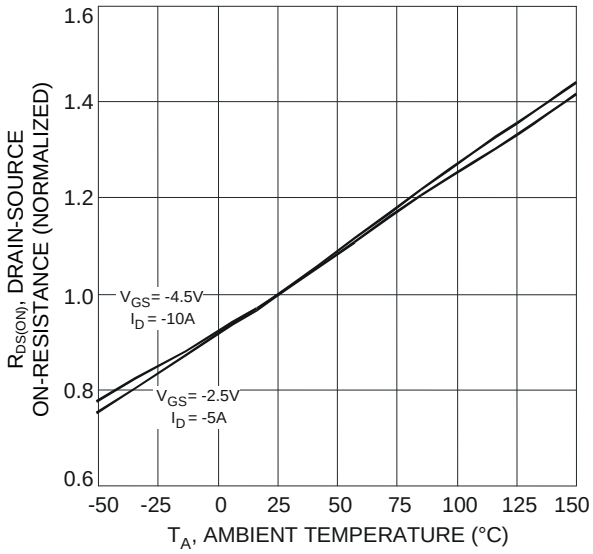


Fig. 5 On-Resistance Variation with Temperature

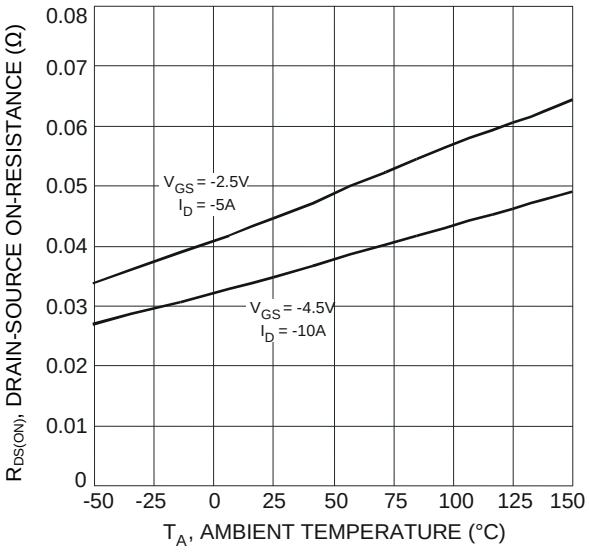


Fig. 6 On-Resistance Variation with Temperature

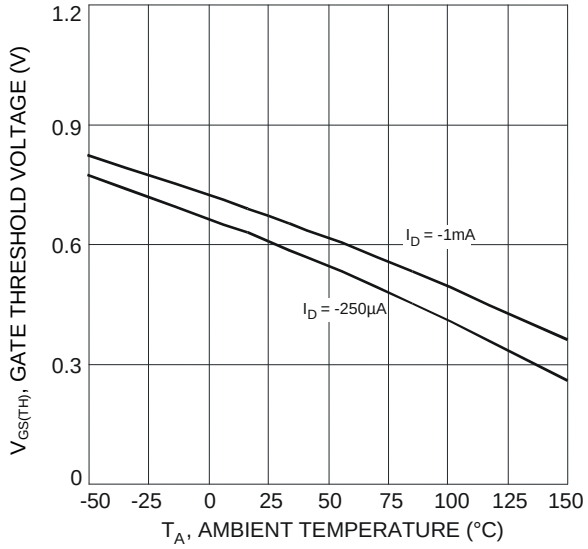


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

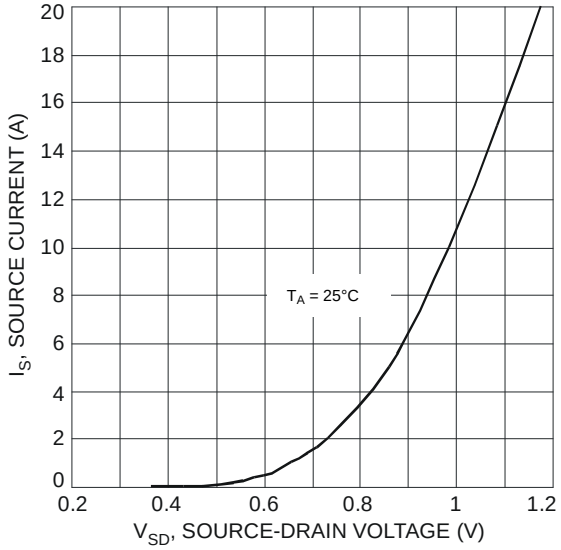


Fig. 8 Diode Forward Voltage vs. Current

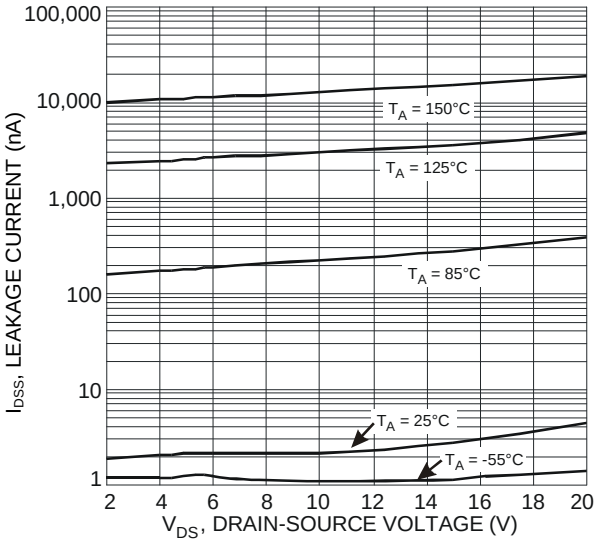


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

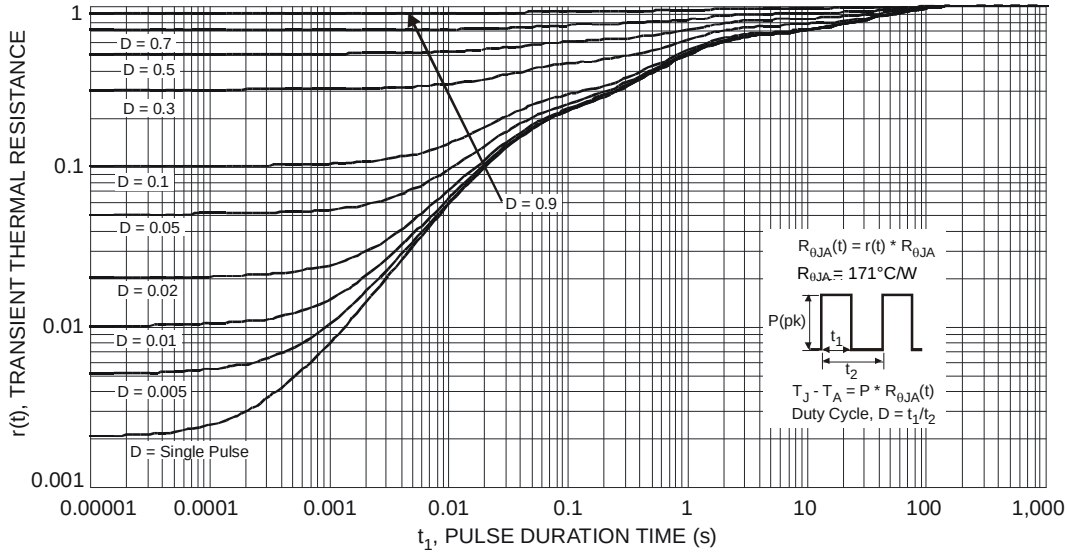
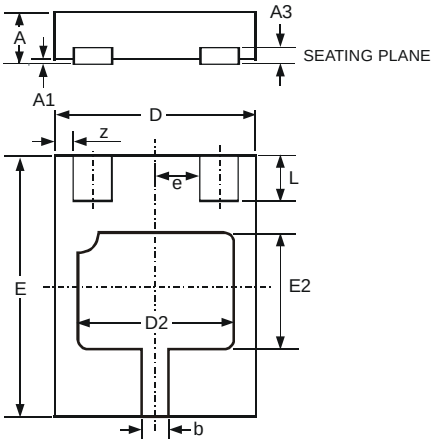


Fig. 10 Transient Thermal Response

Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

X2-DFN2015-3

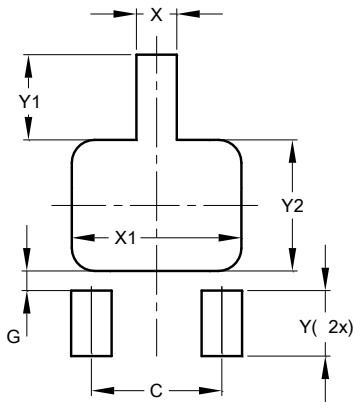


X2-DFN2015-3			
Dim	**Min**	**Max**	**Typ**
A	-	0.40	-
A1	0	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.45	1.575	1.5
D2	1.00	1.20	1.10
e	-	-	0.50
E	1.95	2.075	2.00
E2	0.70	0.90	0.80
L	0.25	0.35	0.30
z	-	-	0.125
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

X2-DFN2015-3



X2-DFN2015-3	
Dimensions	**Value (in mm)**
C	1.000
G	0.150
X	0.310
X1	1.300
Y	0.500
Y1	0.650
Y2	1.000

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